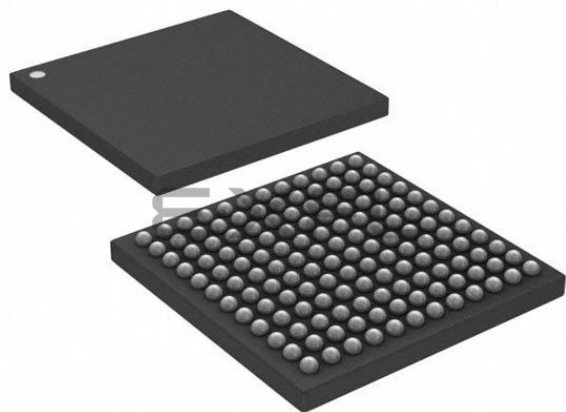




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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	147456
Number of I/O	97
Number of Gates	1000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-55°C ~ 125°C (TJ)
Package / Case	144-LBGA
Supplier Device Package	144-FPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p1000-fg144m

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- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper power-up behavior. Power ramp-up should be monotonic, at least until VCC and VCCPLX exceed brownout activation levels. The VCC activation level is specified as 1.1 V worst-case (see Figure 2-1 and Figure 2-2 on page 2-5 for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels ($0.75\text{ V} \pm 0.25\text{ V}$), the PLL output lock signal goes low and/or the output clock is lost. Refer to the "Power-Up/-Down Behavior of Low-Power Flash Devices" chapter of the *Military ProASIC3/EL FPGA Fabric User's Guide* for information on clock and lock recovery.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers

Output buffers, after 200 ns delay from input buffer activation.

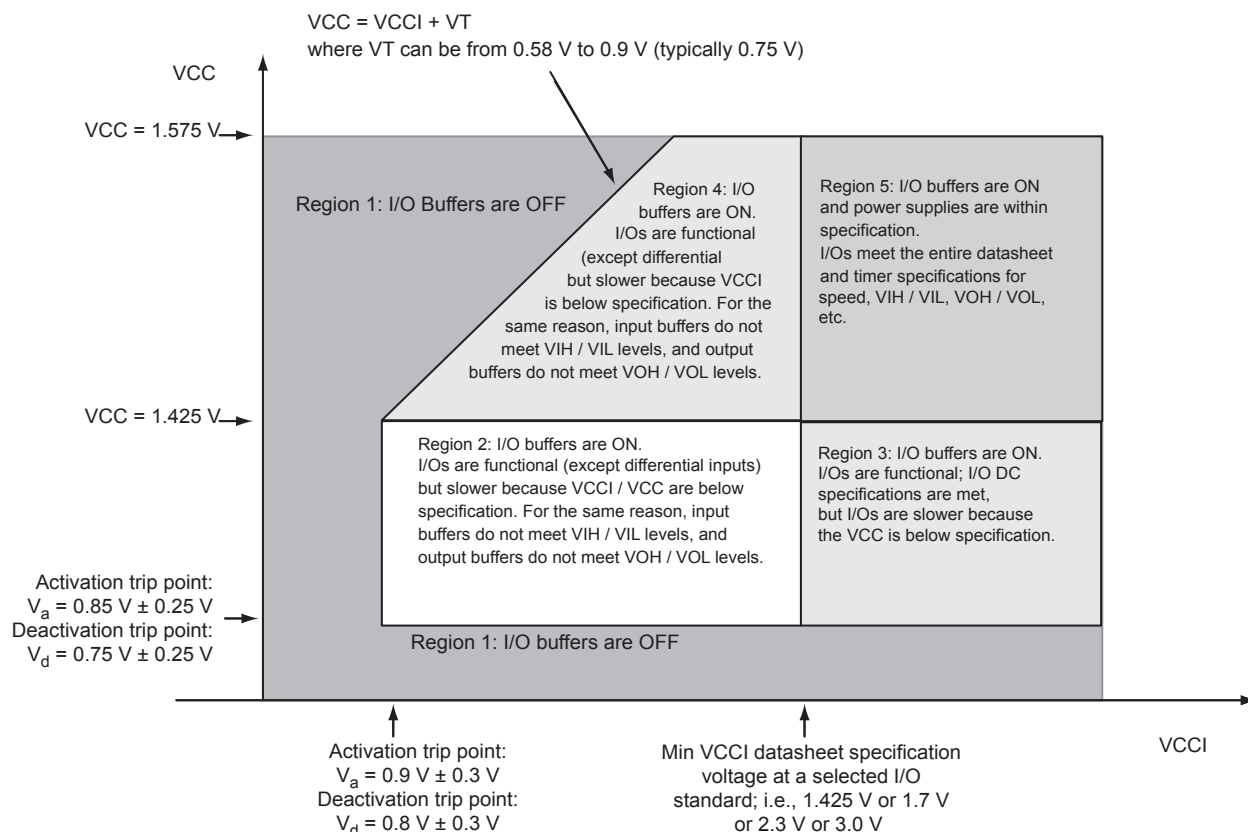


Figure 2-1 • Devices Operating at 1.5 V Core – I/O State as a Function of VCCI and VCC Voltage Levels

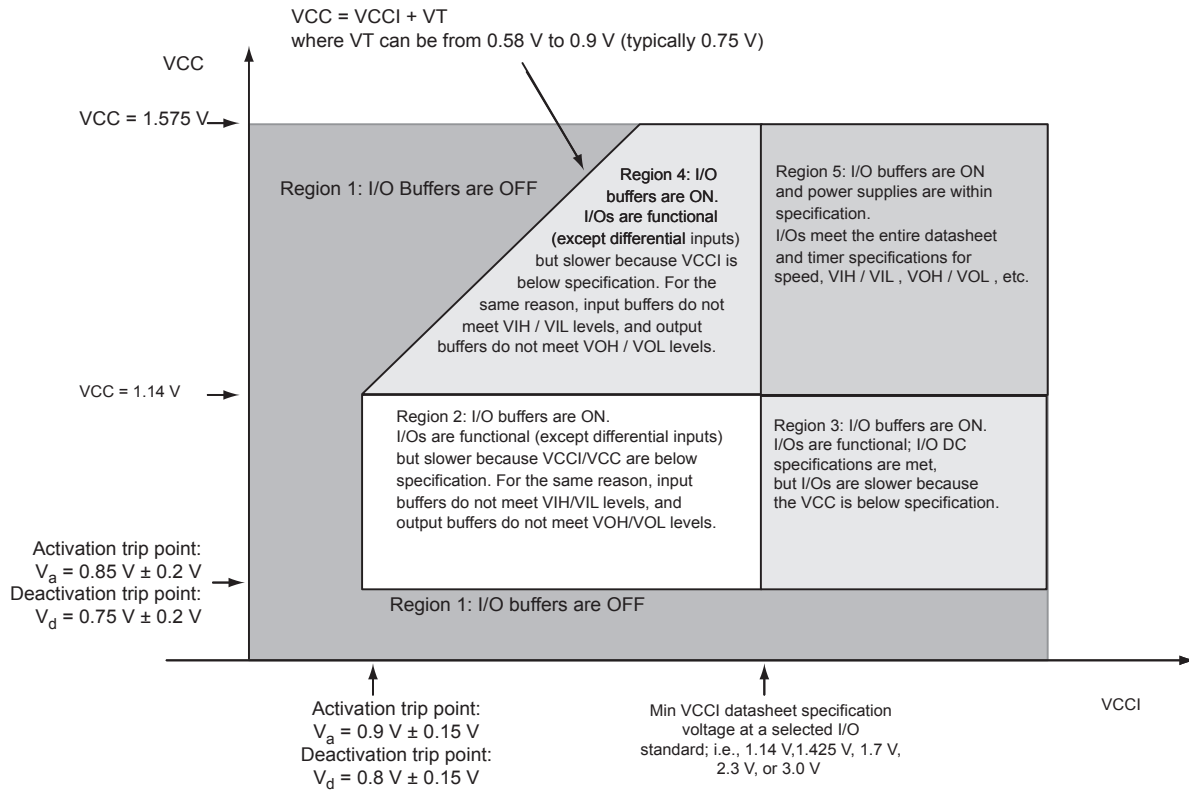


Figure 2-2 • Device Operating at 1.2 V Core Voltage – I/O State as a Function of VCCI and VCC Voltage Levels; Only A3PE600L and A3PE3000L Devices Operate at 1.2 V Core Voltage

Thermal Characteristics

Introduction

The temperature variable in the Designer software refers to the junction temperature, not the ambient temperature. This is an important distinction because dynamic and static power consumption cause the chip junction temperature to be higher than the ambient temperature.

EQ 1 can be used to calculate junction temperature.

$$T_J = \text{Junction Temperature} = \Delta T + T_A$$

EQ 1

where:

T_A = Ambient Temperature

ΔT = Temperature gradient between junction (silicon) and ambient $\Delta T = \theta_{ja} * P$

θ_{ja} = Junction-to-ambient of the package. θ_{ja} numbers are located in Table 2-5.

P = Power dissipation

Package Thermal Characteristics

The device junction-to-case thermal resistivity is θ_{jc} and the junction-to-ambient air thermal resistivity is θ_{ja} . The thermal characteristics for θ_{ja} are shown for two air flow rates. The recommended maximum junction temperature is 125°C. EQ 2 shows a sample calculation of the recommended maximum power dissipation allowed for a 484-pin FBGA package at military temperature and in still air.

$$\text{Maximum Power Allowed} = \frac{\text{Max. junction temp. (}^\circ\text{C)} - \text{Max. ambient temp. (}^\circ\text{C)}}{\theta_{ja}(\text{}^\circ\text{C/W)}} = \frac{125^\circ\text{C} - 70^\circ\text{C}}{20.6^\circ\text{C/W}} = 2.670$$

Calculating Power Dissipation

Quiescent Supply Current

Table 2-8 • Power Supply State Per Mode

	Power Supply Configurations				
Modes/Power Supplies	VCC	VCCPLL	VCCI	VJTAG	VPUMP
Flash*Freeze	On	On	On	On	On/off/floating
Sleep	Off	Off	On	Off	Off
Shutdown	Off	Off	Off	Off	Off
Static and Active	On	On	On	On	On/off/floating

Table 2-9 • Quiescent Supply Current (IDD) Characteristics, Flash*Freeze Mode*

	Core Voltage	A3PE600L	A3PE3000L	Units
Nominal (25°C)	1.2 V	0.55	2.75	mA
	1.5 V	0.83	4.2	mA
Typical maximum (25°C)	1.2 V	9	17	mA
	1.5 V	12	20	mA
Military maximum (125°C)	1.2 V	65	165	mA
	1.5 V	85	185	mA

Note: *IDD includes VCC, VPUMP, VCCI, VJTAG, and VCCPLL currents. Values do not include I/O static contribution (PDC6 and PDC7).

Table 2-10 • Quiescent Supply Current (IDD) Characteristics, Sleep Mode (VCC = 0 V)*

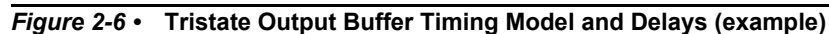
	Core Voltage	A3PE600L	A3PE3000L	Units
VCCI / VJTAG = 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	μA
VCCI / VJTAG = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	μA
VCCI / VJTAG = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	μA
VCCI / VJTAG = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	μA
VCCI / VJTAG = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	μA

Note: *IDD = $N_{BANKS} \times ICCI$. Values do not include I/O static contribution, which is shown in Table 2-22 on page 2-14 (PDC6 and PDC7).

Table 2-11 • Quiescent Supply Current (IDD) Characteristics, Shutdown Mode*

	Core Voltage	A3P250	A3P1000	A3PE600L	A3PE3000L	Units
Nominal (25°C)	1.2 V / 1.5 V	N/A		0		μA
Military (125°C)	1.2 V / 1.5 V	N/A		0		μA

Note: *This is applicable to A3PE600L and A3PE3000L only for cold-sparable I/O devices. Not available on A3P250 or A3P1000.



Overview of I/O Performance

Summary of I/O DC Input and Output Levels – Default I/O Software Settings

Table 2-25 • Summary of Maximum and Minimum DC Input and Output Levels
 Applicable to Military Conditions—Software Default Settings
 Applicable to Pro I/Os for A3PE600L and A3PE3000L Only

I/O Standard	Drive Strength	Equiv. Software Default Drive Strength Option ¹	Slew Rate	VIL		VIH		VOL	VOH	I _{OL} ²	I _{OH} ²
				Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTTL / 3.3 V LVCMOS	12 mA	12 mA	High	–0.3	0.8	2	3.6	0.4	2.4	12	12
3.3 V LVCMOS Wide Range ^{1,3}	100 µA	12 mA	High	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	0.1	0.1
2.5 V LVCMOS	12 mA	12 mA	High	–0.3	0.7	1.7	3.6	0.7	1.7	12	12
1.8 V LVCMOS	12 mA	12 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	12	12
1.5 V LVCMOS	12 mA	12 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	12	12
1.2 V LVCMOS ^{4,5}	2 mA	2 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVCMOS Wide Range ^{1,4,5}	100 µA	2 mA	High	–0.3	0.3 * VCCI	0.7 * VCCI	3.6	0.1	VCCI – 0.1	0.1	0.1
3.3 V PCI	Per PCI Specification										
3.3 V PCI-X	Per PCI-X Specification										
3.3 V GTL	20 mA ⁶	20 mA	High	–0.3	VREF – 0.05	VREF + 0.05	3.6	0.4	–	20	20
2.5 V GTL	20 mA ⁶	20 mA	High	–0.3	VREF – 0.05	VREF + 0.05	3.6	0.4	–	20	20
3.3 V GTL+	35 mA	35 mA	High	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.6	–	35	35
2.5 V GTL+	33 mA	33 mA	High	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.6	–	33	33
HSTL (I)	8 mA	8 mA	High	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.4	VCCI – 0.4	8	8
HSTL (II)	15 mA ⁶	15 mA ⁶	High	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.4	VCCI – 0.4	15	15
SSTL2 (I)	15 mA	15 mA	High	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.54	VCCI – 0.62	15	15
SSTL2 (II)	18 mA	18 mA	High	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.35	VCCI – 0.43	18	18
SSTL3 (I)	14 mA	14 mA	High	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.7	VCCI – 1.1	14	14
SSTL3 (II)	21 mA	21 mA	High	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.5	VCCI – 0.9	21	21

Notes:

- Note that 1.2 V LVCMOS and 3.3 V LVCMOS wide range is applicable to 100 µA drive strength only. The configuration will not operate at the equivalent software default drive strength. These values are for normal ranges only.
- Currents are measured at 125°C junction temperature.
- All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
- Applicable to A3PE600L and A3PE3000L devices operating at VCCI ≥ VCC.
- All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.
- Output drive strength is below JEDEC specification.
- Output slew rate can be extracted using the IBIS Models.

2.5 V LVCMOS

Low-Voltage CMOS for 2.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 2.5 V applications.

Table 2-70 • Minimum and Maximum DC Input and Output Levels
Applicable to Pro I/Os for A3PE600L and A3PE3000L Only

2.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
4 mA	−0.3	0.7	1.7	3.6	0.7	1.7	4	4	16	18	15	15
8 mA	−0.3	0.7	1.7	3.6	0.7	1.7	8	8	32	37	15	15
12 mA	−0.3	0.7	1.7	3.6	0.7	1.7	12	12	65	74	15	15
16 mA	−0.3	0.7	1.7	3.6	0.7	1.7	16	16	83	87	15	15
24 mA	−0.3	0.7	1.7	3.6	0.7	1.7	24	24	169	124	15	15

Notes:

1. I_{IL} is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. I_{IH} is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 125°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-71 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

2.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.7	1.7	2.7	0.7	1.7	2	2	16	18	15	15
4 mA	−0.3	0.7	1.7	2.7	0.7	1.7	4	4	16	18	15	15
6 mA	−0.3	0.7	1.7	2.7	0.7	1.7	6	6	32	37	15	15
8 mA	−0.3	0.7	1.7	2.7	0.7	1.7	8	8	32	37	15	15
12 mA	−0.3	0.7	1.7	2.7	0.7	1.7	12	12	65	74	15	15
16 mA	−0.3	0.7	1.7	2.7	0.7	1.7	16	16	83	87	15	15
24 mA	−0.3	0.7	1.7	2.7	0.7	1.7	24	24	169	124	15	15

Notes:

1. I_{IL} is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. I_{IH} is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 125°C junction temperature.
5. Software default selection highlighted in gray.

1.5 V DC Core Voltage

Table 2-88 • 1.8 V LVCMOS Low Slew

Military-Case Conditions: $T_J = 125^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.7\text{ V}$
Applicable to Pro I/Os for A3PE600L and A3PE3000L Only

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.61	9.02	0.04	1.69	2.52	0.40	9.17	7.57	2.61	1.01	10.63	9.04	ns
	–1	0.52	7.68	0.03	1.44	2.14	0.34	7.80	6.44	2.22	0.86	9.04	7.69	ns
4 mA	Std.	0.61	7.41	0.04	1.69	2.52	0.40	7.52	6.36	3.07	2.56	8.99	7.83	ns
	–1	0.52	6.30	0.03	1.44	2.14	0.34	6.40	5.41	2.62	2.18	7.64	6.66	ns
6 mA	Std.	0.61	6.26	0.04	1.69	2.52	0.40	6.35	5.53	3.38	3.14	7.82	7.00	ns
	–1	0.52	5.33	0.03	1.44	2.14	0.34	5.40	4.71	2.88	2.67	6.65	5.95	ns
8 mA	Std.	0.61	5.88	0.04	1.69	2.52	0.40	5.96	5.37	3.45	3.30	7.42	6.83	ns
	–1	0.52	5.00	0.03	1.44	2.14	0.34	5.07	4.57	2.94	2.81	6.32	5.81	ns
12 mA	Std.	0.61	5.76	0.04	1.69	2.52	0.40	5.85	5.38	3.55	3.88	7.31	6.84	ns
	–1	0.52	4.90	0.03	1.44	2.14	0.34	4.97	4.57	3.02	3.30	6.22	5.82	ns
16 mA	Std.	0.61	5.76	0.04	1.69	2.52	0.40	5.85	5.38	3.55	3.88	7.31	6.84	ns
	–1	0.52	4.90	0.03	1.44	2.14	0.34	4.97	4.57	3.02	3.30	6.22	5.82	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-89 • 1.8 V LVCMOS High Slew

Military-Case Conditions: $T_J = 125^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.7\text{ V}$
Applicable to Pro I/Os for A3PE600L and A3PE3000L Only

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.61	4.01	0.04	1.69	2.52	0.40	4.06	3.94	2.60	1.03	5.52	5.40	ns
	–1	0.52	3.41	0.03	1.44	2.14	0.34	3.45	3.35	2.21	0.88	4.70	4.60	ns
4 mA	Std.	0.61	3.22	0.04	1.69	2.52	0.40	3.26	2.89	3.07	2.65	4.72	4.36	ns
	–1	0.52	2.74	0.03	1.44	2.14	0.34	2.77	2.46	2.61	2.26	4.02	3.71	ns
6 mA	Std.	0.61	2.74	0.04	1.69	2.52	0.40	2.77	2.38	3.38	3.23	4.23	3.84	ns
	–1	0.52	2.33	0.03	1.44	2.14	0.34	2.36	2.02	2.88	2.75	3.60	3.27	ns
8 mA	Std.	0.61	2.65	0.04	1.69	2.52	0.40	2.68	2.28	3.45	3.40	4.14	3.75	ns
	–1	0.52	2.26	0.03	1.44	2.14	0.34	2.28	1.94	2.93	2.89	3.52	3.19	ns
12 mA	Std.	0.61	2.64	0.04	1.69	2.52	0.40	2.66	2.16	3.55	4.01	4.13	3.63	ns
	–1	0.52	2.24	0.03	1.44	2.14	0.34	2.26	1.84	3.02	3.41	3.51	3.08	ns
16 mA	Std.	0.61	2.64	0.04	1.69	2.52	0.40	2.66	2.16	3.55	4.01	4.13	3.63	ns
	–1	0.52	2.24	0.03	1.44	2.14	0.34	2.26	1.84	3.02	3.41	3.51	3.08	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Timing Characteristics

1.2 V DC Core Voltage

Table 2-108 • 1.2 V LVCMOS Low Slew

Military-Case Conditions: $T_J = 125^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V
Applicable to Pro I/O Banks for A3PE600L and A3PE3000L Only

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.80	12.61	0.05	2.65	3.75	0.52	12.10	9.50	5.11	4.66	14.31	11.71	ns
	–1	0.68	10.72	0.05	2.25	3.19	0.44	10.30	8.08	4.35	3.97	12.17	9.96	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-109 • 1.2 V LVCMOS High Slew

Military-Case Conditions: $T_J = 125^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V
Applicable to Pro I/O Banks for A3PE600L and A3PE3000L Only

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Unit s
2 mA	Std.	0.80	5.16	0.05	2.65	3.75	0.52	4.98	4.39	5.10	4.81	7.19	6.60	ns
	–1	0.68	4.39	0.05	2.25	3.19	0.44	4.24	3.74	4.34	4.09	6.11	5.61	ns

Notes:

- Software default selection highlighted in gray.
- For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

B-LVDS/M-LVDS

Bus LVDS (B-LVDS) and Multipoint LVDS (M-LVDS) specifications extend the existing LVDS standard to high-performance multipoint bus applications. Multidrop and multipoint bus configurations may contain any combination of drivers, receivers, and transceivers. Microsemi LVDS drivers provide the higher drive current required by B-LVDS and M-LVDS to accommodate the loading. The drivers require series terminations for better signal quality and to control voltage swing. Termination is also required at both ends of the bus since the driver can be located anywhere on the bus. These configurations can be implemented using the TRIBUF_LVDS and BIBUF_LVDS macros along with appropriate terminations. Multipoint designs using Microsemi LVDS macros can achieve up to 200 MHz with a maximum of 20 loads. A sample application is given in [Figure 2-26](#). The input and output buffer delays are available in the LVDS section in [Table 2-160 on page 2-86](#).

Example: For a bus consisting of 20 equidistant loads, the following terminations provide the required differential voltage, in worst-case Industrial operating conditions, at the farthest receiver: $R_S = 60\ \Omega$ and $R_T = 70\ \Omega$, given $Z_0 = 50\ \Omega$ (2") and $Z_{stub} = 50\ \Omega$ (~1.5").

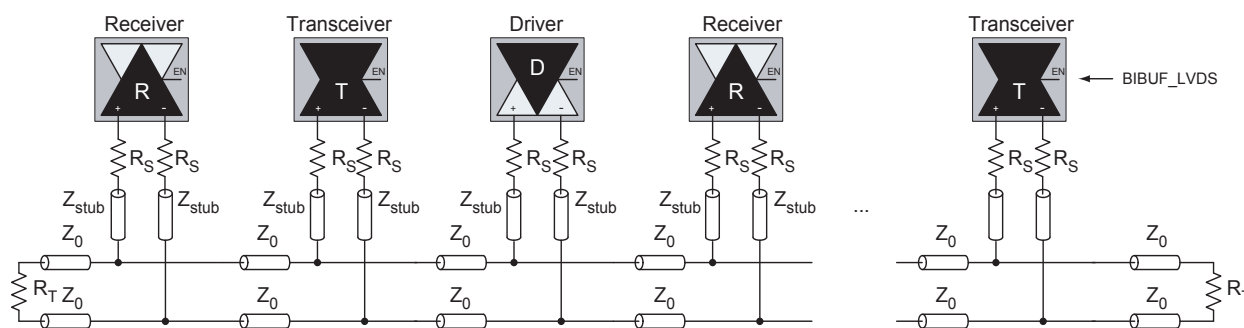


Figure 2-26 • B-LVDS/M-LVDS Multipoint Application Using LVDS I/O Buffers

Input Register

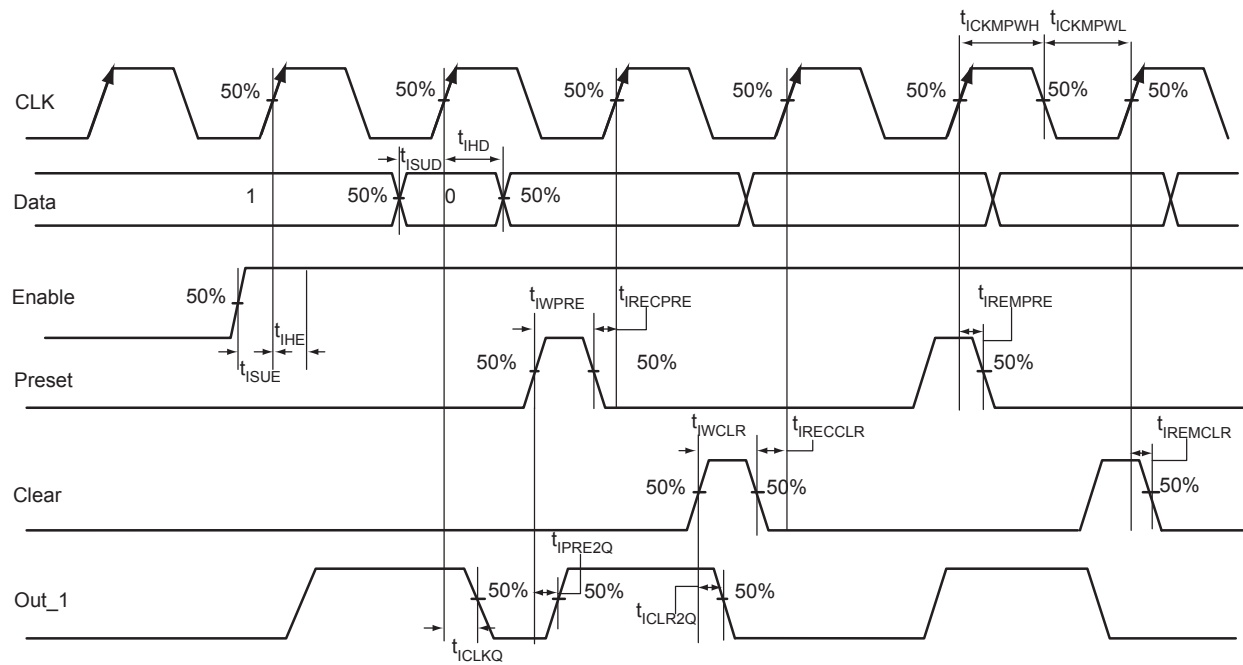


Figure 2-30 • Input Register Timing Diagram

1.5 V DC Core Voltage

Table 2-197 • A3PE600L Global Resource
Military-Case Conditions: $T_J = 125^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	–1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.82	1.07	0.97	1.26	ns
t_{RCKH}	Input High Delay for Global Clock	0.81	1.10	0.95	1.30	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock					ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock					ns
t_{RCKSW}	Maximum Skew for Global Clock		0.30		0.35	ns
F_{RMAX}	Maximum Frequency for Global Clock					MHz

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-198 • A3PE3000L Global Resource
Military-Case Conditions: $T_J = 125^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	–1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	1.62	1.87	1.90	2.20	ns
t_{RCKH}	Input High Delay for Global Clock	1.61	1.90	1.89	2.24	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock					ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock					ns
t_{RCKSW}	Maximum Skew for Global Clock		0.30		0.35	ns
F_{RMAX}	Maximum Frequency for Global Clock					MHz

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-207 • RAM512X18
Military-Case Conditions: $T_J = 125^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$ for A3PE600L and A3PE3000L

Parameter	Description	–1	Std.	Units
t_{AS}	Address setup time	0.26	0.31	ns
t_{AH}	Address hold time	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.10	0.11	ns
t_{ENH}	REN, WEN hold time	0.06	0.07	ns
t_{DS}	Input data (WD) setup time	0.19	0.23	ns
t_{DH}	Input data (WD) hold time	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained, WMODE = 0)	2.29	2.69	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	0.95	1.12	ns
t_{C2CRWH}	Address collision clk-to-clk delay for reliable read access after write on same address – applicable to opening edge	0.18	0.21	ns
t_{C2CWRH}	Address collision clk-to-clk delay for reliable write access after read on same address – applicable to opening edge	0.21	0.25	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow through)	0.98	1.15	ns
	RESET Low to data out Low on RD (pipelined)	0.98	1.15	ns
$t_{REMRSTB}$	RESET removal	0.30	0.36	ns
$t_{RECRSTB}$	RESET recovery	1.59	1.87	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.59	0.67	ns
t_{CYC}	Clock cycle time	5.39	6.20	ns
F_{MAX}	Maximum frequency	185	161	MHz

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

FIFO

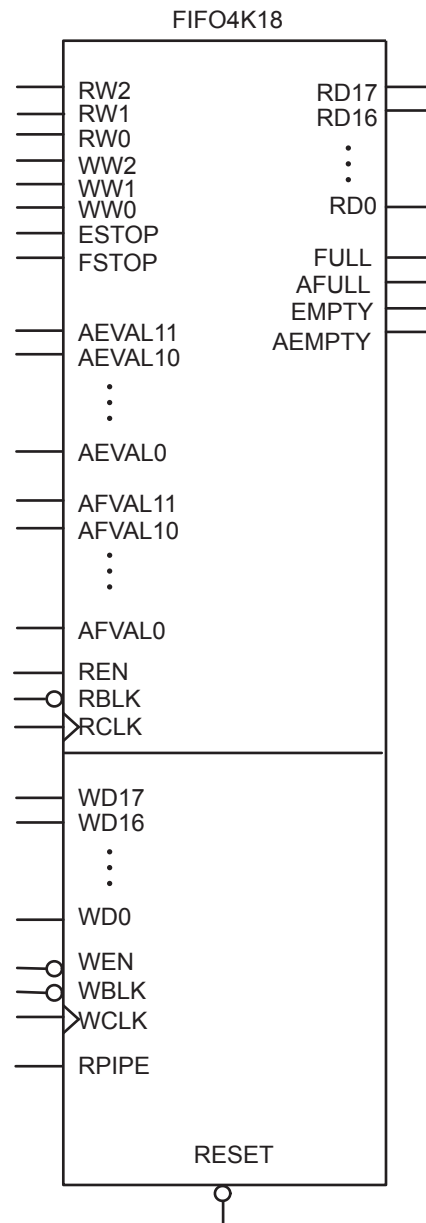


Figure 2-49 • FIFO Model

JTAG 1532 Characteristics

JTAG timing delays do not include JTAG I/Os. To obtain complete JTAG timing, add I/O buffer delays to the corresponding standard selected; refer to the I/O timing characteristics in the "User I/O Characteristics" section on page 2-18 for more details.

Timing Characteristics

Table 2-220 • JTAG 1532

Military-Case Conditions: $T_J = 125^\circ\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$ for A3PE600L and A3PE3000L

Parameter	Description	–1	Std.	Units
t_{DISU}	Test Data Input Setup Time	0.80	0.94	ns
t_{DIHD}	Test Data Input Hold Time	1.60	1.88	ns
t_{TMSU}	Test Mode Select Setup Time	0.80	0.94	ns
t_{TMDHD}	Test Mode Select Hold Time	1.60	1.88	ns
t_{TCK2Q}	Clock to Q (data out)	6.39	7.52	ns
t_{RSTB2Q}	Reset to Q (data out)	26.63	31.33	ns
F_{TCKMAX}	TCK Maximum Frequency	18.70	15.90	MHz
t_{TRSTREM}	ResetB Removal Time	0.48	0.56	ns
t_{TRSTREC}	ResetB Recovery Time	0.00	0.00	ns
t_{TRSTMPW}	ResetB Minimum Pulse	TBD	TBD	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-221 • JTAG 1532

Military-Case Conditions: $T_J = 125^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$ for All Dies

Parameter	Description	–1	Std.	Units
t_{DISU}	Test Data Input Setup Time	0.60	0.71	ns
t_{DIHD}	Test Data Input Hold Time	1.21	1.42	ns
t_{TMSU}	Test Mode Select Setup Time	0.60	0.71	ns
t_{TMDHD}	Test Mode Select Hold Time	1.21	1.42	ns
t_{TCK2Q}	Clock to Q (data out)	6.04	7.10	ns
t_{RSTB2Q}	Reset to Q (data out)	24.15	28.41	ns
F_{TCKMAX}	TCK Maximum Frequency	22.00	19.00	MHz
t_{TRSTREM}	ResetB Removal Time	0.00	0.00	ns
t_{TRSTREC}	ResetB Recovery Time	0.24	0.28	ns
t_{TRSTMPW}	ResetB Minimum Pulse	TBD	TBD	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

3 – Pin Descriptions and Packaging

Supply Pins

GND**Ground**

Ground supply voltage to the core, I/O outputs, and I/O logic.

GNDQ**Ground (quiet)**

Quiet ground supply voltage to input buffers of I/O banks. Within the package, the GNDQ plane is decoupled from the simultaneous switching noise originated from the output buffer ground domain. This minimizes the noise transfer within the package and improves input signal integrity. GNDQ must always be connected to GND on the board.

VCC**Core Supply Voltage**

Supply voltage to the FPGA core, nominally 1.5 V for A3P250 and A3P100 devices and 1.2 V or 1.5 V for A3PE600L and A3PE3000L devices. VCC is required for powering the JTAG state machine in addition to VJTAG. Even when a device is in bypass mode in a JTAG chain of interconnected devices, both VCC and VJTAG must remain powered to allow JTAG signals to pass through the device.

For A3PE600L and A3PE3000L devices, VCC can be switched dynamically from 1.2 V to 1.5 V or vice versa. This allows in-system programming (ISP) when VCC is at 1.5 V and the benefit of low power operation when VCC is at 1.2 V.

VCCIBx**I/O Supply Voltage**

Supply voltage to the bank's I/O output buffers and I/O logic. Bx is the I/O bank number. There are up to eight I/O banks on low power flash devices plus a dedicated VJTAG bank. Each bank can have a separate VCCI connection. All I/Os in a bank will run off the same VCCIBx supply. VCCI can be 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VCCI pins tied to GND.

VMVx**I/O Supply Voltage (quiet)**

Quiet supply voltage to the input buffers of each I/O bank. x is the bank number. Within each I/O bank, the VMV and VCCI are connected to each other to improve the ESD discharge path for any I/O pin against its VMV pin. Each bank must have at least one VMV connection, and no VMV should be left unconnected. All I/Os in a bank run off the same VMVx supply. VMV is used to provide a quiet supply voltage to the input buffers of each I/O bank. VMVx can be 1.2 V (A3PE600L and A3PE3000L only), 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VMV pins tied to GND. VMV and VCCI should be at the same voltage within a given I/O bank. Used VMV pins must be connected to the corresponding VCCI pins of the same bank (i.e., VMV0 to VCCIB0, VMV1 to VCCIB1, etc.).

VCCPLA/B/C/D/E/F**PLL Supply Voltage**

Supply voltage to analog PLL, nominally 1.5 V or 1.2 V, depending on the device.

- 1.5 V for A3P250 and A3P1000 devices
- 1.2 V or 1.5 V for A3PE600L or A3PE3000L devices

When the PLLs are not used, the Microsemi Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground. Microsemi recommends tying VCCPLx to VCC and using proper filtering circuits to decouple VCC noise from the PLLs. Refer to the PLL Power Supply Decoupling section of the "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" chapter of the *Military ProASIC3/EL Device Family User's Guide* for a complete board solution for the PLL analog power supply and ground.

- There is one VCCPLF pin on A3P250 and A3P1000 devices.
- There are six VCCPLX pins on A3PE600L and A3PE3000L devices.

FG256	
Pin Number	A3P1000 Function
H3	GFB1/IO208PPB3
H4	VCOMPLF
H5	GFC0/IO209NPB3
H6	VCC
H7	GND
H8	GND
H9	GND
H10	GND
H11	VCC
H12	GCC0/IO91NPB1
H13	GCB1/IO92PPB1
H14	GCA0/IO93NPB1
H15	IO96NPB1
H16	GCB0/IO92NPB1
J1	GFA2/IO206PSB3
J2	GFA1/IO207PDB3
J3	VCCPLF
J4	IO205NDB3
J5	GFB2/IO205PDB3
J6	VCC
J7	GND
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO95PPB1
J13	GCA1/IO93PPB1
J14	GCC2/IO96PPB1
J15	IO100PPB1
J16	GCA2/IO94PSB1
K1	GFC2/IO204PDB3
K2	IO204NDB3
K3	IO203NDB3
K4	IO203PDB3
K5	VCCIB3
K6	VCC
K7	GND
K8	GND

FG256	
Pin Number	A3P1000 Function
K9	GND
K10	GND
K11	VCC
K12	VCCIB1
K13	IO95NPB1
K14	IO100NPB1
K15	IO102NDB1
K16	IO102PDB1
L1	IO202NDB3
L2	IO202PDB3
L3	IO196PPB3
L4	IO193PPB3
L5	VCCIB3
L6	GND
L7	VCC
L8	VCC
L9	VCC
L10	VCC
L11	GND
L12	VCCIB1
L13	GDB0/IO112NPB1
L14	IO106NDB1
L15	IO106PDB1
L16	IO107PDB1
M1	IO197NSB3
M2	IO196NPB3
M3	IO193NPB3
M4	GEC0/IO190NPB3
M5	VMV3
M6	VCCIB2
M7	VCCIB2
M8	IO147RSB2
M9	IO136RSB2
M10	VCCIB2
M11	VCCIB2
M12	VMV2
M13	IO110NDB1
M14	GDB1/IO112PPB1

FG256	
Pin Number	A3P1000 Function
M15	GDC1/IO111PDB1
M16	IO107NDB1
N1	IO194PSB3
N2	IO192PPB3
N3	GEC1/IO190PPB3
N4	IO192NPB3
N5	GNDQ
N6	GEA2/IO187RSB2
N7	IO161RSB2
N8	IO155RSB2
N9	IO141RSB2
N10	IO129RSB2
N11	IO124RSB2
N12	GNDQ
N13	IO110PDB1
N14	VJTAG
N15	GDC0/IO111NDB1
N16	GDA1/IO113PDB1
P1	GEB1/IO189PDB3
P2	GEB0/IO189NDB3
P3	VMV2
P4	IO179RSB2
P5	IO171RSB2
P6	IO165RSB2
P7	IO159RSB2
P8	IO151RSB2
P9	IO137RSB2
P10	IO134RSB2
P11	IO128RSB2
P12	VMV1
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO113NDB1
R1	GEA1/IO188PDB3
R2	GEA0/IO188NDB3
R3	IO184RSB2
R4	GEC2/IO185RSB2

FG484		FG484	
Pin Number	A3P1000 Function	Pin Number	A3P1000 Function
Y3	NC	AA16	IO122RSB2
Y4	IO182RSB2	AA17	IO119RSB2
Y5	GND	AA18	IO117RSB2
Y6	IO177RSB2	AA19	NC
Y7	IO174RSB2	AA20	NC
Y8	VCC	AA21	VCCIB1
Y9	VCC	AA22	GND
Y10	IO154RSB2	AB1	GND
Y11	IO148RSB2	AB2	GND
Y12	IO140RSB2	AB3	VCCIB2
Y13	NC	AB4	IO180RSB2
Y14	VCC	AB5	IO176RSB2
Y15	VCC	AB6	IO173RSB2
Y16	NC	AB7	IO167RSB2
Y17	NC	AB8	IO162RSB2
Y18	GND	AB9	IO156RSB2
Y19	NC	AB10	IO150RSB2
Y20	NC	AB11	IO145RSB2
Y21	NC	AB12	IO144RSB2
Y22	VCCIB1	AB13	IO132RSB2
AA1	GND	AB14	IO127RSB2
AA2	VCCIB3	AB15	IO126RSB2
AA3	NC	AB16	IO123RSB2
AA4	IO181RSB2	AB17	IO121RSB2
AA5	IO178RSB2	AB18	IO118RSB2
AA6	IO175RSB2	AB19	NC
AA7	IO169RSB2	AB20	VCCIB2
AA8	IO166RSB2	AB21	GND
AA9	IO160RSB2	AB22	GND
AA10	IO152RSB2		
AA11	IO146RSB2		
AA12	IO139RSB2		
AA13	IO133RSB2		
AA14	NC		
AA15	NC		

FG484		FG484		FG484	
Pin Number	A3PE3000L Function	Pin Number	A3PE3000L Function	Pin Number	A3PE3000L Function
C18	GND	E9	IO22NDB0V2	F22	IO98NDB2V2
C19	IO76PPB1V4	E10	IO30NDB0V3	G1	IO289NDB7V1
C20	IO88NDB2V0	E11	IO38PDB0V4	G2	IO289PDB7V1
C21	IO94PPB2V1	E12	IO44NDB1V0	G3	IO291PPB7V2
C22	VCCIB2	E13	IO58NDB1V2	G4	IO295PDB7V2
D1	IO293PDB7V2	E14	IO58PDB1V2	G5	IO297PDB7V2
D2	IO303NDB7V3	E15	GBC1/IO79PDB1V4	G6	GAC2/IO307PDB7V4
D3	IO305NDB7V3	E16	GGB0/IO80NDB1V4	G7	VCOMPLA
D4	GND	E17	GNDQ	G8	GNDQ
D5	GAA0/IO00NDB0V0	E18	GBA2/IO82PDB2V0	G9	IO26NDB0V3
D6	GAA1/IO00PDB0V0	E19	IO86NDB2V0	G10	IO26PDB0V3
D7	GAB0/IO01NDB0V0	E20	GND	G11	IO36PDB0V4
D8	IO20PDB0V2	E21	IO90NDB2V1	G12	IO42PDB1V0
D9	IO22PDB0V2	E22	IO98PDB2V2	G13	IO50PDB1V1
D10	IO30PDB0V3	F1	IO299NPB7V3	G14	IO60NDB1V2
D11	IO38NDB0V4	F2	IO301NDB7V3	G15	GNDQ
D12	IO52NDB1V1	F3	IO301PDB7V3	G16	VCOMPLB
D13	IO52PDB1V1	F4	IO308NDB7V4	G17	GGB2/IO83PDB2V0
D14	IO66NDB1V3	F5	IO309NDB7V4	G18	IO92PDB2V1
D15	IO66PDB1V3	F6	VMV7	G19	IO92NDB2V1
D16	GGB1/IO80PDB1V4	F7	VCCPLA	G20	IO102PDB2V2
D17	GBA0/IO81NDB1V4	F8	GAC0/IO02NDB0V0	G21	IO102NDB2V2
D18	GBA1/IO81PDB1V4	F9	GAC1/IO02PDB0V0	G22	IO105NDB2V2
D19	GND	F10	IO32NDB0V3	H1	IO286PSB7V1
D20	IO88PDB2V0	F11	IO32PDB0V3	H2	IO291NPB7V2
D21	IO90PDB2V1	F12	IO44PDB1V0	H3	VCC
D22	IO94NPB2V1	F13	IO50NDB1V1	H4	IO295NDB7V2
E1	IO293NDB7V2	F14	IO60PDB1V2	H5	IO297NDB7V2
E2	IO299PPB7V3	F15	GBC0/IO79NDB1V4	H6	IO307NDB7V4
E3	GND	F16	VCCPLB	H7	IO287PDB7V1
E4	GAB2/IO308PDB7V4	F17	VMV2	H8	VMV0
E5	GAA2/IO309PDB7V4	F18	IO82NDB2V0	H9	VCCIB0
E6	GNDQ	F19	IO86PDB2V0	H10	VCCIB0
E7	GAB1/IO01PDB0V0	F20	IO96PDB2V1	H11	IO36NDB0V4
E8	IO20NDB0V2	F21	IO96NDB2V1	H12	IO42NDB1V0

FG896	
Pin Number	A3PE3000L Function
H26	IO84NDB2V0
H27	IO96PDB2V1
H28	IO96NDB2V1
H29	IO89PDB2V0
H30	IO89NDB2V0
J1	IO290NDB7V2
J2	IO290PDB7V2
J3	IO302NDB7V3
J4	IO302PDB7V3
J5	IO295NDB7V2
J6	IO299NDB7V3
J7	VCCIB7
J8	VCCPLA
J9	VCC
J10	IO04NPB0V0
J11	IO18NDB0V2
J12	IO20NDB0V2
J13	IO20PDB0V2
J14	IO32NDB0V3
J15	IO32PDB0V3
J16	IO42PDB1V0
J17	IO44NDB1V0
J18	IO44PDB1V0
J19	IO54NDB1V1
J20	IO54PDB1V1
J21	IO76NPB1V4
J22	VCC
J23	VCCPLB
J24	VCCIB2
J25	IO90PDB2V1
J26	IO90NDB2V1
J27	GBB2/IO83PDB2V0
J28	IO83NDB2V0
J29	IO91PDB2V1
J30	IO91NDB2V1
K1	IO288NDB7V1